

IN THE CLAIMS

Please cancel claim 4 without prejudice and amend claims 1, 9, 14, 15, 16 and 17

as follows:

B1 SUB C1
1. A solid state p-n heterojunction comprising an electron conductor in the solid state and a hole conductor, further comprising a sensitising semiconductor, said sensitizing semiconductor being located at an interface between said electron conductor and said hole conductor, characterised in that said hole conductor is in the solid state, in that said sensitizing semiconductor is in a form consisting of individual particles adsorbed at the surface of said electron conductor, said individual particles being quantum dots, and in that said p-n heterojunction comprises a plurality of individual point-contact heterojunctions between said quantum dots and said electron conductor and said hole conductor.

B2 SUB C3
9. A heterojunction as claimed in claim 1, characterised in that said hole conductor is an amorphous reversibly oxydisable organic or organometallic compound.

B3
14. A solid state sensitized photovoltaic cell comprising a solid state p-n heterojunction as claimed in claim 1.

15. A cell as claimed in claim 14, characterised in that it comprises
a transparent first electrode,
a said solid state p-n heterojunction and
a second electrode.

16. A cell as claimed in claim 15, further comprising a dense semiconductive layer between said first electrode and said solid state p-n heterojunction.

Cont
B3

SUB
C5 7

17. A cell as claimed in claim 14, characterised in that said solid state p-n heterojunction is obtained by forming quantum dots on the surface of said electron conductor by at least one deposition treatment, before providing said hole conductor to said layered heterojunction.
